

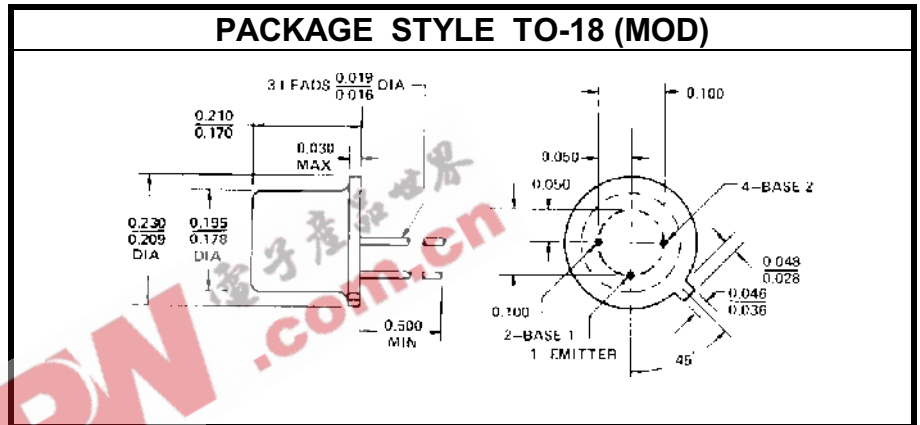
SILICON PN UNIJUNCTION TRANSISTOR

DESCRIPTION:

The **2N2646** is a Unijunction Transistor Used in General Purpose Pulse, Timing, Sense and Trigger Applications.

MAXIMUM RATINGS

I_C	2.0 A (PULSED)
V_{CE}	30 V
P_{DISS}	300 mW @ T _C = 25 °C
T_J	-65 °C to +125 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	33 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
η	V _{B2B1} = 10 V	0.56		0.75	--
r_{BB}	V _{B2B1} = 3.0 V	4.7		9.1	KΩ
α_{rBB}	V _{B2B1} = 3.0 V T _A = -55 to 125 °C	0.1		0.9	%/°C
V_{EB1(SAT)}	V _{B2B1} = 10 V I _E = 50 mA		3.0		V
I_{B2(MOD)}	V _{B2B1} = 10 V I _E = 50 mA		20		mA
I_{B2EO}	V _{B2E} = 30 V I _{B1} = 0			12	μA
I_P	V _{B2B1} = 25 V			5.0	μA
I_V	V _{B2B1} = 20 V R _{B2} = 100 Ω	4.0			mA
V_{OB1}	V _{B2B1} = 20 V R _{B1} = 20 Ω	3.0	5.0		V